

## **NCE N-Channel Super Trench Power MOSFET**

## **Description**

The NCEP40T15AGU uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification

## **Application**

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

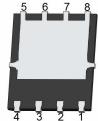
#### **General Features**

- $V_{DS}$  =40V, $I_D$  =150A  $R_{DS(ON)}$ =1.15m $\Omega$  , typical@  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 150°C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

### DFN5X6

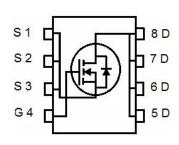




 1
 2
 3
 4
 3
 2
 1

 Top View

 Bottom View



**Schematic Diagram** 

## **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P40T15AGU	NCEP40T15AGU	DFN5X6-8L	-	-	-

## Absolute Maximum Ratings (T<sub>c</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	40	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous	I <sub>D</sub>	150	Α
Drain Current-Continuous(T <sub>C</sub> =100℃)	I <sub>D</sub> (100℃)	106	А
Pulsed Drain Current	I <sub>DM</sub>	600	Α
Maximum Power Dissipation	P <sub>D</sub>	135	W
Derating factor		1.1	W/℃
Single pulse avalanche energy (Note 1)	Eas	1344	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	°C

## **Thermal Characteristic**

Thermal Resistance, Junction-to-Case	R <sub>eJC</sub>	0.93	°C/W
·			1

# NCEP40T15AGU

## Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	,			•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	40		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics	·					
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =75A	-	1.15	1.45	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =75A		80	-	S
Dynamic Characteristics						
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V, F=1.0MHz	-	4135	-	PF
Output Capacitance	Coss		-	2110	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	120	-	PF
Switching Characteristics (Note 2)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	9	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =20 $V$ , $I_D$ =75 $A$	-	6	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}\text{=}10V, R_{G}\text{=}1.6\Omega$	-	42	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	8	-	nS
Total Gate Charge	Qg	\/ 00\/ L 75A	-	62	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}=20V, I_{D}=75A,$	-	19.7	-	nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V	-	14.4	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =75A	-		1.2	V
Diode Forward Current	Is		-	-	150	Α
Reverse Recovery Time	t <sub>rr</sub>	$T_J = 25^{\circ}C$ , $I_F = I_S$	-		30	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs	-		110	nC

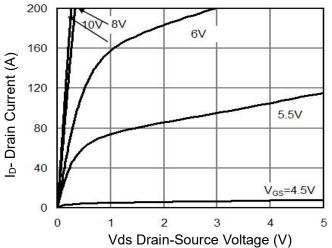
## Notes:

<sup>1.</sup> EAS condition : Tj=25  $^{\circ}\text{C}$  ,VDD=20V,VG=10V,L=0.5mH,Rg=25 $\Omega$ 

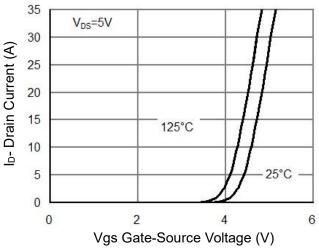
<sup>2.</sup> Guaranteed by design, not subject to production

<sup>3.</sup> These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of TJ(MAX)=150° C. The SOA curve provides a single pulse rating.





**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

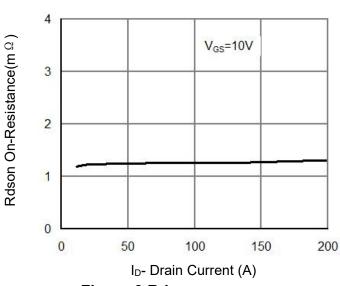


Figure 3 Rdson- Drain Current

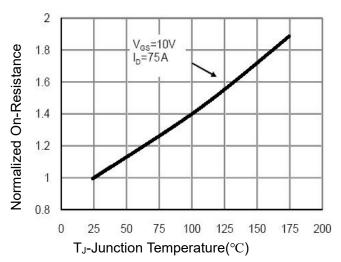


Figure 4 Rdson-JunctionTemperature

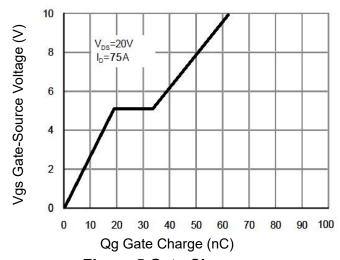
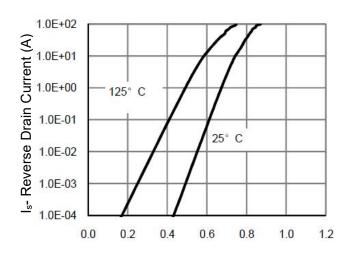


Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward

0.01

1E-05

0.0001

0.001

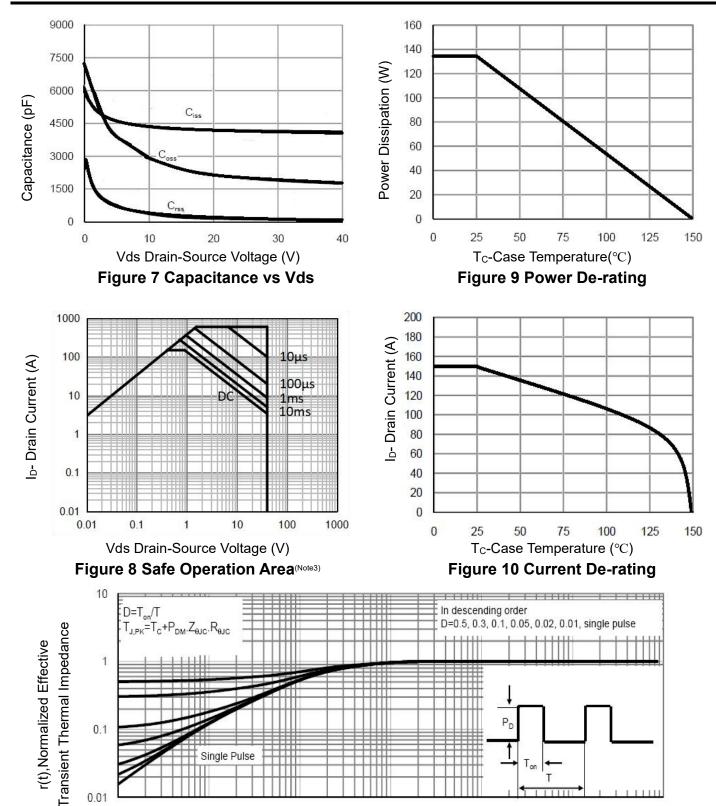


Figure 11 Normalized Maximum Transient Thermal Impedance

Square Wave Pluse Duration(sec)

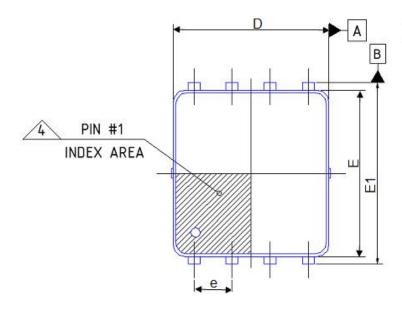
0.01

0.1

1

10

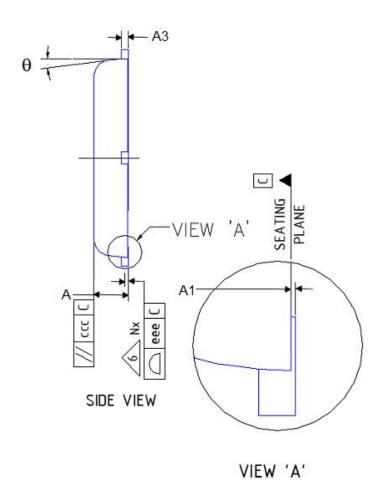
# DFN5X6-8L(f) Package Information



ddd M Nxb S(N) T

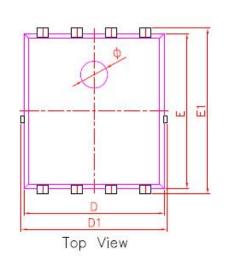
TOP VIEW

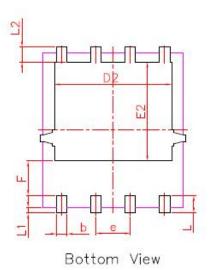
BOTTOM VIEW

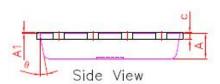


	D	imension	Table	
Thickness Symbol	V			NOTE
upol 3	MINIMUM	NOMINAL	MAXIMUM	
Α	0.85	0.95	1.00	
A1	0.00		0.05	
A3		0.2 Ref	1	
Ь	0.30	0.40	0.50	
D	5.10	5.20	5.30	
E	5.45	5.55	5.65	
е		1.27 BSC		
D1	4.25	4.35	4.45	
E1	5.95	6.05	6.15	
E2	3.525	3.625	3.725	
E3	1.175	1.275	1.375	
L	0.45	0.55	0.65	
L1	0		0.15	
L2		0.68 REF		
θ	0°		10°	
aaa		0.05		
bbb	Ì	0.10	T	
ccc		0.10		
ddd		0.05		
eee	0.08			
N	N 8 ND 4			
ND				
NOTES		1,2		

# DFN5X6-8L(E) Package Information

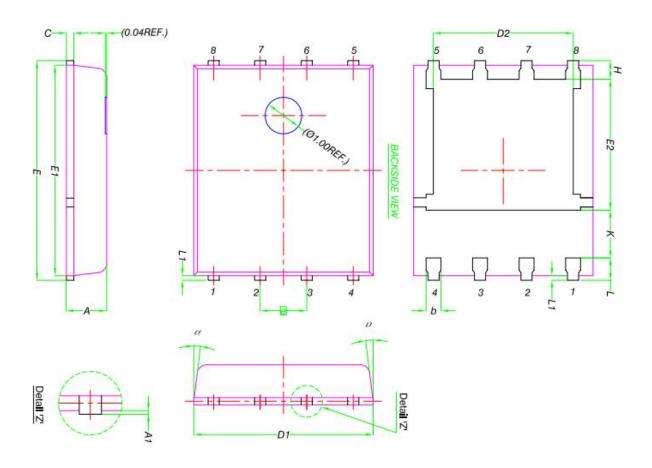




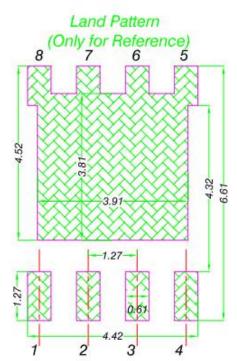


DIM.	MIN.	NOM.	MAX.	
Α	0.90	0.95	1.00	
A1	0.00	0.02	0.05	
b	0.35	0.40	0.50	
С	0.20	0.25	0.30	
D	5.10	5.20	5.30	
D1	5.10	5.40	5.50	
D2	4.25	4.35	4.45	
е		1.27 BSC	BSC	
Ε	5.70	5.75	5.80	
E1	6.00	6.15	6.30	
E2	3.57	3.67	3.77	
F	1.18	1.28	1.38	
L	0.55	0.65	0.75	
L1	0.15	0.20	0.25	
L2	0.45	0.55	0.65	
Ø	0.90	1.00	1.10	
Θ	8.	10"	12*	

# DFN5X6-8L (G) Package Information



	MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	
Α	0.90	1.00	1.10	
A1	0	-	0.05	
b	0.33	0.41	0.51	
С	0.20	0.25	0.30	
D1	4.80	4.90	5.00	
D2	3.61	3.81	3.96	
Ε	5.90	6.00	6.10	
E1	5.70	5.75	5.80	
E2	3.38	3.58	3.78	
е		1.27 BSC		
Н	0.41	0.51	0.61	
K	1.10	-	-	
L	0.51	0.61	0.71	
L1	0.06	0.13	0.20	
α	0°	15	12°	



# NCEP40T15AGU

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